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BD911 (NPN) & BD912 (PNP) Silicon Complementary Transistors Audio Power Amp, Switch TO-220 Type Package

Description:

The BD911 (NPN) and BD912 (PNP) are silicon complementary power transistors in a TO-220 plastic package intended for use in power amplifier and switching applications.

Absolute Maximum Ratings:

| | |
|--------------------------------------------------------------------|-------------------------------------|
| Collector-Emitter Voltage, V_{CEO} | 100V |
| Collector-Base Voltage, V_{CBO} | 100V |
| Emitter-Base Voltage, V_{EBO} | 5V |
| Collector Current, I_C | |
| Continuous | 15A |
| Peak | 20A |
| Base Current, I_B | 5A |
| Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D | 90W |
| Derate Above $+25^\circ\text{C}$ | 0.72W/ $^\circ\text{C}$ |
| Operating Junction Temperature Range, T_J | -65° to $+150^\circ\text{C}$ |
| Storage Temperature Range, T_{stg} | -65° to $+150^\circ\text{C}$ |
| Thermal Resistance Junction-to-Case, R_{thJC} | 1.38 $^\circ\text{C}/\text{W}$ Max |

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------|---------------------------------------|-----|-----|-----|------|
| OFF Characteristics | | | | | | |
| Collector-Emitter Sustaining Voltage | $V_{CEO(sus)}$ | $I_B = 0, I_C = 50\text{mA}$, Note 1 | 100 | - | - | V |
| Collector Cutoff Current | I_{CEO} | $I_B = 0, V_{CE} = 50\text{V}$ | - | - | 1 | mA |
| | I_{CBO} | $I_E = 0, V_{CB} = 100\text{V}$ | - | - | 0.5 | mA |
| Emitter Cutoff Current | I_{EBO} | $I_C = 0, V_{EB} = 5\text{V}$ | - | - | 1 | mA |

Note 1. Pulse Test; Pulse width = 300 μs , Duty Cycle \leq 2%.

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|----------------------------------------------------------------------|-----|-----|-----|------|
| ON Characteristics (Note 1) | | | | | | |
| DC Current Gain | h_{FE} | $I_C = 0.5\text{A}, V_{CE} = 4\text{V}$ | 40 | - | 250 | |
| | | $I_C = 5\text{A}, V_{CE} = 4\text{V}$ | 15 | - | 150 | |
| | | $I_C = 10\text{A}, V_{CE} = 4\text{V}$ | 5 | - | - | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 5\text{A}, I_B = 0.5\text{A}$ | - | - | 1 | V |
| | | $I_C = 10\text{A}, I_B = 2.5\text{A}$ | - | - | 3 | V |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C = 10\text{A}, I_B = 2.5\text{A}$ | - | - | 2.5 | V |
| Base-Emitter ON Voltage | $V_{BE(on)}$ | $I_C = 5\text{A}, V_{CE} = 4\text{V}$ | - | - | 1.5 | V |
| Dynamic Characteristics | | | | | | |
| Current Gain-Bandwidth Product | f_T | $I_C = 500\text{mA}, V_{CE} = 4\text{V}, f = 1\text{MHz},$ Note 2 | 3 | - | - | MHz |

Note 1. Pulse Test; Pulse width = $300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Note 2. $f_T = |h_{fe}| \cdot f_{test}$.

